

PNP Transistors

—PNP Silicon—

■■ APPLICATION: High Current Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

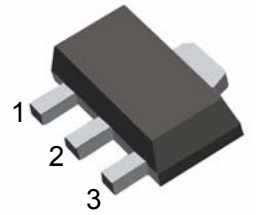
PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	VCBO	-40	V
Collector-emitter voltage	VCEO	-25	V
Emitter-base voltage	VEBO	-6	V
Collector current	Ic	-1.5	A
Collector Power Dissipation	Pc	-1	W
Junction Temperature	Tj	150	°C
Storage Temperature Range	Tstg	-55-150	°C

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER


■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
Collector-Base Breakdown Voltage	BVcbo	-40			V	Ic=-0.1 mA Ie=0
Collector-Emitter Breakdown Voltage	BVceo	-25			V	Ic=-2 mA Ib=0
Emitter-Base Breakdown Voltage	BVebo	-6			V	Ie=-0.1 mA Ic=0
Collector Cut-off Current	Icbo			-0.1	uA	Vcb=-35 V Ie=0
Emitter Cut-off Current	Iebo			-0.1	uA	Veb=-6 V Ic=0
Collector-Emitter Saturation Voltage	Vce(sat)			-0.5	V	Ic=-800mA Ib=-80mA
Base-Emitter Saturation Voltage	Vbe(sat)			-1.2	V	Ic=-800mA Ib=-80mA
DC Current Gain	h _{FE}	100		300	β	Vce=-2 V Ic=-100 mA
Gain bandwidth product	fT	100	200		MHz	Vce=-10 V Ic=-50 mA
Common Base Output Capacitance	Cob		15	30	pF	Vcb=-10 V Ie=0 f=1MHz

■■ h_{FE} Classification And Marking

Print Mark	HC	HD
Classification	C	D
h _{FE}	100-200	160-320